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Vishay Semiconductors

## **Thyristor Surface Mount Phase Control SCR, 16 A**



PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub>	10 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	1600 V						
V <sub>TM</sub>	1.4 V						
I <sub>GT</sub>	60 mA						
$T_J$	-40 °C to +125 °C						
Package	D <sup>2</sup> PAK (TO-263AB)						
Circuit configuration	Single SCR						

#### **FEATURES**

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

### ROHS COMPLIANT HALOGEN FREE

#### **APPLICATIONS**

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are in identical package outlines

#### **DESCRIPTION**

The VS-16TTS16S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5							
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	6.3	9.5	А						
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	14.0	18.5							

### Note

•  $T_A = 55 \, ^{\circ}\text{C}$ ,  $T_J = 125 \, ^{\circ}\text{C}$ , footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	10	^						
I <sub>RMS</sub>		16	- A						
V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V						
I <sub>TSM</sub>		200	Α						
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		-40 to +125	°C						

<b>VOLTAGE RATINGS</b>			
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA
VS-16TTS16S-M3	1600	1600	10



ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL		TEST CONDITIONS	VAL	UNITS			
PARAMETER	STIMBUL		TEST CONDITIONS	TYP.	MAX.	UNITS		
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 18	0° conduction, half sine wave	1	0			
Maximum RMS on-state current	I <sub>RMS</sub>			1	6	А		
Maximum peak, one-cycle,	1	10 ms sine pul	lse, rated V <sub>RRM</sub> applied	17	70	A		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pul	lse, no voltage reapplied	20	00			
Maximum 12t for funing	l <sup>2</sup> t	10 ms sine pul	lse, rated V <sub>RRM</sub> applied	14	14	A2a		
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine pul	10 ms sine pulse, no voltage reapplied			A <sup>2</sup> s		
Maximum l <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 1	0 ms, no voltage reapplied	2000		A²√s		
Maximum on-state voltage drop	V <sub>TM</sub>	10 A, T <sub>J</sub> = 25 °	°C	1.4		V		
On-state slope resistance	r <sub>t</sub>	T 105 °C		24.0		mΩ		
Threshold voltage	V <sub>T(TO)</sub>	$T_{\rm J} = 125  ^{\circ}{\rm C}$	I <sub>J</sub> = 125 ·C		.1	V		
Maximum reverse and direct leakage current	1/1	T <sub>J</sub> = 25 °C	$V_R = \text{rated } V_{RRM} / V_{DRM}$	0.	.5			
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	T <sub>J</sub> = 125 °C		10				
Holding current	l <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C			150	mA		
Maximum latching current	ΙL	Anode supply	200					
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max. linear to 80 % $V_{DRM} = R_g - k = open$			00	V/µs		
Maximum rate of rise of turned-on current	dI/dt		15	A/µs				

TRIGGERING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum peak gate power	$P_{GM}$		8.0	W					
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV					
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α					
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V					
		Anode supply = 6 V, resistive load, $T_J$ = - 10 °C	90						
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	S V, resistive load, T <sub>J</sub> = 25 °C 60						
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35						
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	3.0						
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	V					
Voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V					
Maximum DC gate voltage not to trigger	$V_{GD}$	T = 125 °C V = reted value	0.25						
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value	2.0	mA					

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9	
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	4	μs
Typical turn-off time	tq	1J = 125 C	110	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	RAMETER SYMBOL TEST CONDITIONS VALUES UN								
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C					
Maximum thermal resistance, junction to case		DC operation	1.3	°C/W					
Typical thermal resistance, junction to ambient R <sub>thJA</sub>		PCB mount <sup>(1)</sup>	40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	oz.					
Marking device Case style D <sup>2</sup> PAK (TO-263AB) 16TTS163									

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

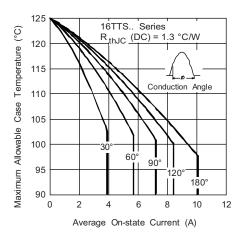


Fig. 1 - Current Rating Characteristics

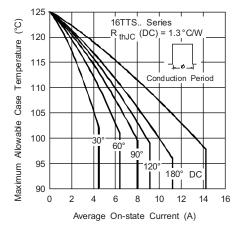


Fig. 2 - Current Rating Characteristics

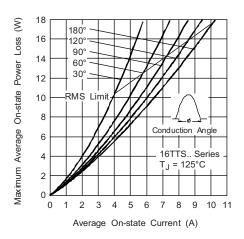


Fig. 3 - On-State Power Loss Characteristics

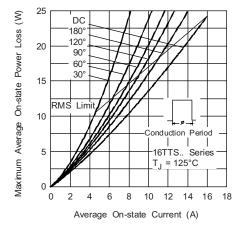


Fig. 4 - On-State Power Loss Characteristics

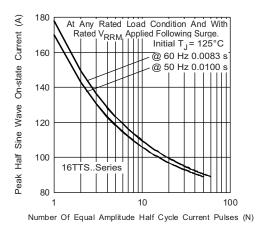


Fig. 5 - Maximum Non-Repetitive Surge Current

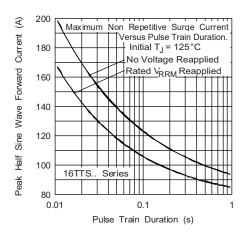


Fig. 6 - Maximum Non-Repetitive Surge Current

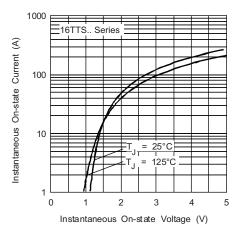


Fig. 7 - On-State Voltage Drop Characteristics

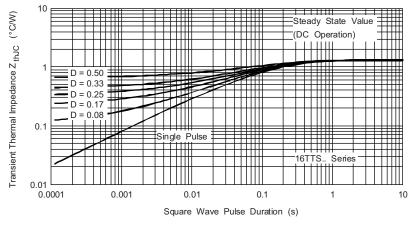


Fig. 8 - Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

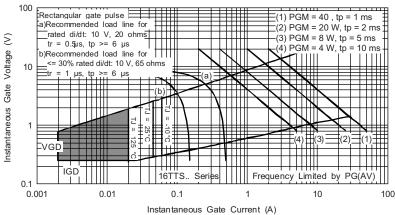
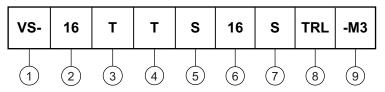


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

### **Device code**



- Vishay Semiconductors product
- 2 Current rating
- 3 Circuit configuration:

T = single thyristor

- 4 Package:
  - $T = D^2PAK (TO-263AB)$
- 5 Type of silicon:
  - S = standard recovery rectifier
- 6 Voltage rating: Voltage code x 100 = V<sub>RRM</sub> (16 = 1600 V)
- 7 S = surface mountable
- 8 • None = tube
  - TRL = tape and reel (left oriented)
  - TRR = tape and reel (right oriented)
- 9 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	PACKAGING DESCRIPTION							
VS-16TTS16S-M3	50	Antistatic plastic tubes						
VS-16TTS16STRL-M3	800	13" diameter plastic tape and reel						
VS-16TTS16STRR-M3	800	13" diameter plastic tape and reel						

LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?96164</u>						
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					



### D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

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